

< Small Signal InGaP HBT >

MGF3021AM

4pin flat lead package

DESCRIPTION

The MGF3021AM InGaP-HBT(Heterojunction Bipolar Transistor) is designed for use in L to C band amplifiers.

The 4pin flat lead package is small-thin size, and offers high cost performance.

FEATURES

$G_{LP}=22\text{dB}$, $P_{1\text{dB}}=11.0\text{dBm}$, $OIP3=24.0\text{dBm}$
 @ $f=2.4\text{GHz}$, $V_{CE}=3\text{V}$, $I_C=14\text{mA}$

APPLICATION

L to C band low noise amplifiers

QUALITY GRADE

GG

RECOMMENDED BIAS CONDITIONS

$V_{CE}=3\text{V}$, $I_C=14\text{mA}$

Outline Drawing

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ABSOLUTE MAXIMUM RATINGS

($T_a=25^\circ\text{C}$)

Symbol	Parameter	Ratings	Unit
V_{CBO}	Collector to Base voltage	12.0V	V
V_{CEO}	Collector to Emitter voltage	4.0V	V
V_{EBO}	Emitter to Base voltage	2.0V	V
I_C	Collector current	20	mA
I_B	Base current	10	mA
PT	Total power dissipation	80	mW
T_{ch}	Channel temperature	150	$^\circ\text{C}$
T_{stg}	Storage temperature	-40 to +125	$^\circ\text{C}$

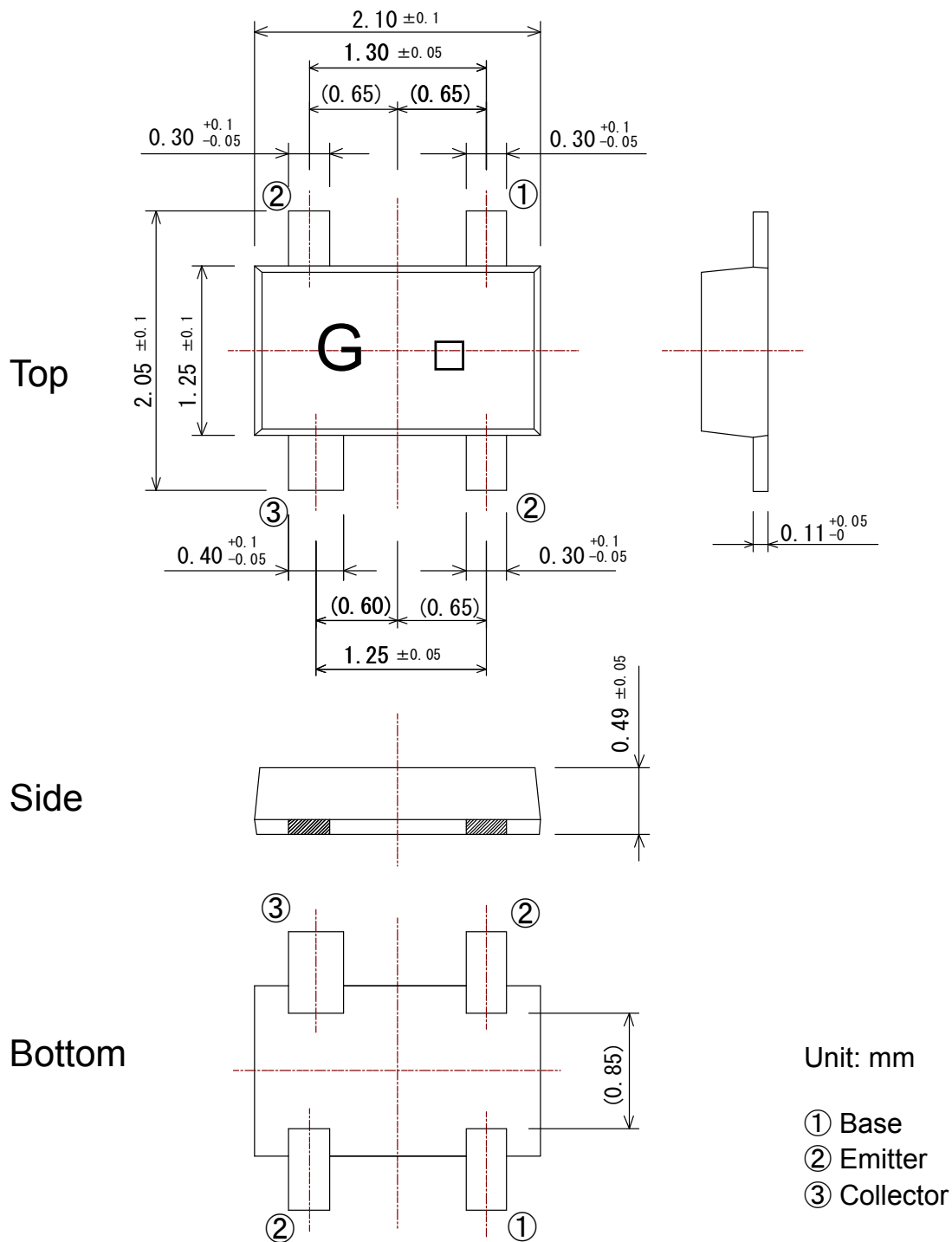
ELECTRICAL CHARACTERISTICS

($T_a=25^\circ\text{C}$)

Symbol	Parameter	Test conditions	Limits			Unit
			MIN.	TYP.	MAX.	
h_{FE}	DC Current Gain	$V_{CE}=3\text{V}$, $I_C=14\text{mA}$	90	110	130	
G_{LP}	Linear Power Gain	$V_{CE}=3\text{V}$, $I_C=14\text{mA}$ $f=2.4\text{GHz}$	19.5	22	--	dB
$P_{1\text{dB}}$	Output power at 1dB gain compression		9.5	11	--	dBm
OIP_3	3rd Order Intermodulation Distortion Output Intercept Point		--	24	--	dBm
G_s	Associated gain	$V_{CE}=3\text{V}$, $I_C=4\text{mA}$ $f=2.4\text{GHz}$	--	17	--	dB
$NF_{min.}$	Minimum noise figure		--	1.2	--	dB

Note 1: OIP_3 , G_s and $NF_{min.}$ @2.4GHz are not tested.

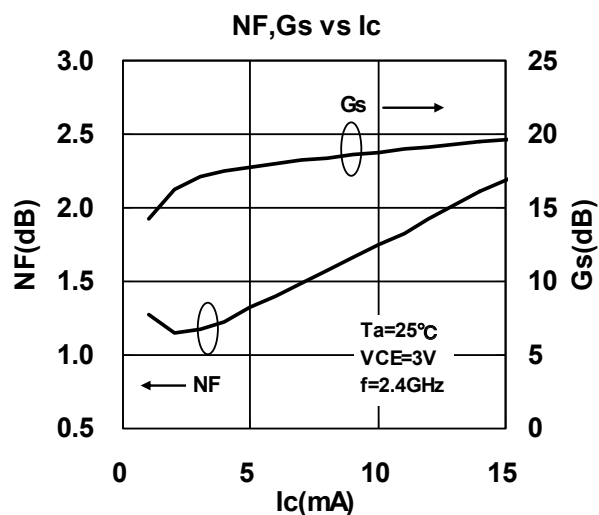
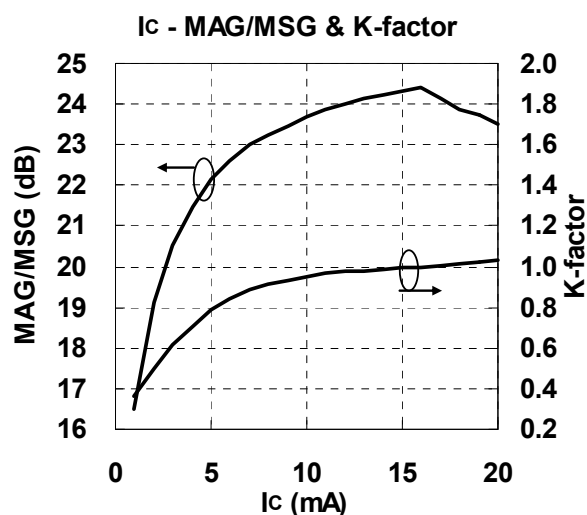
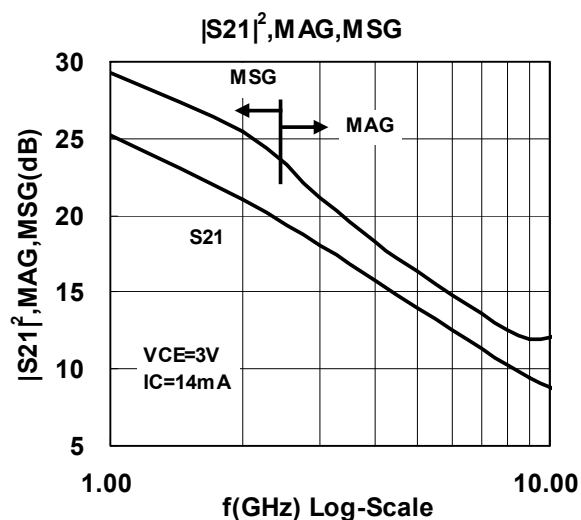
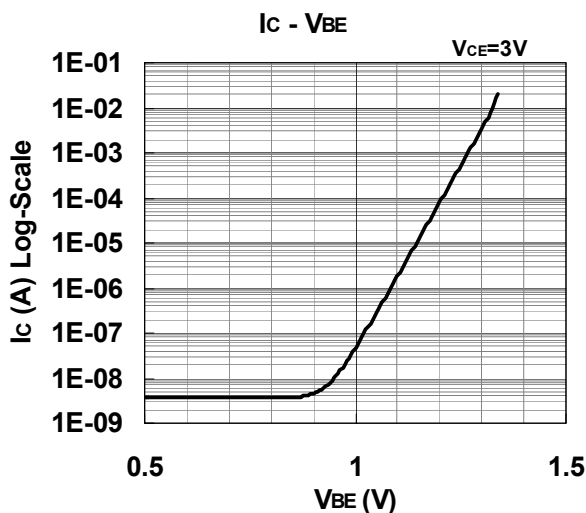
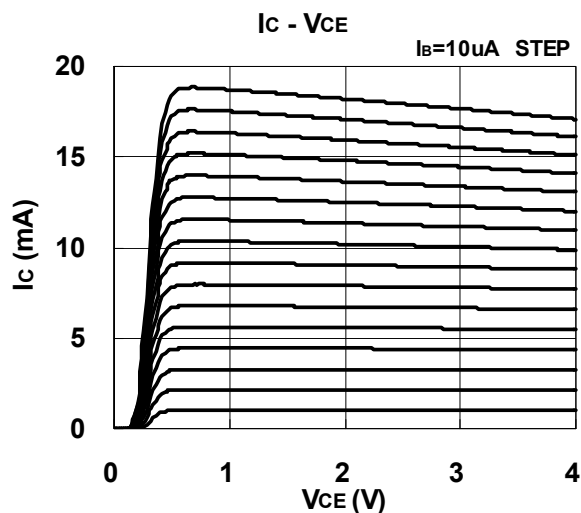
Note 2: G_{LP} and $P_{1\text{dB}}$ @2.4GHz are tested with sampling inspection.



(GD-30)

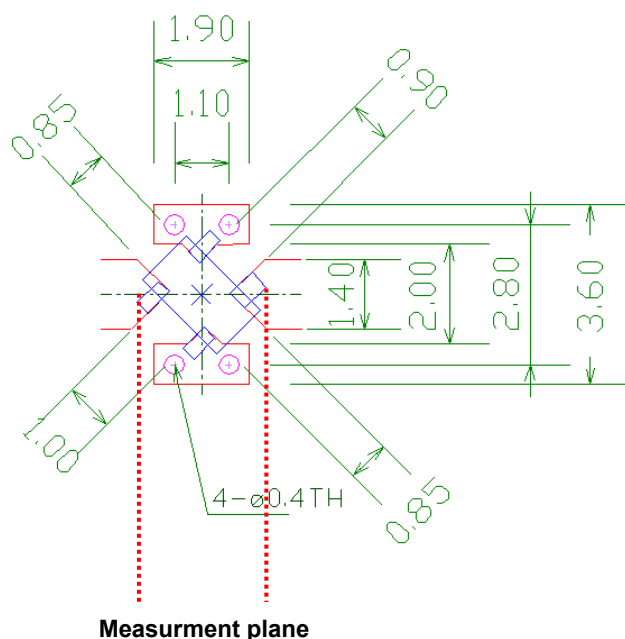
(Reference data)

TYPICAL CHARACTERISTICS (Ta=25°C)



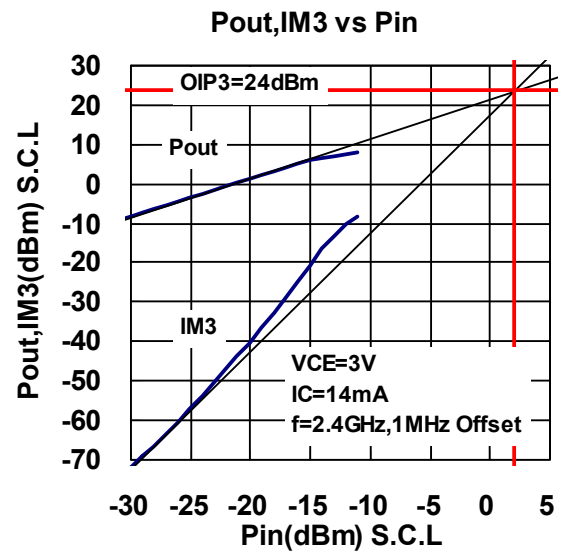
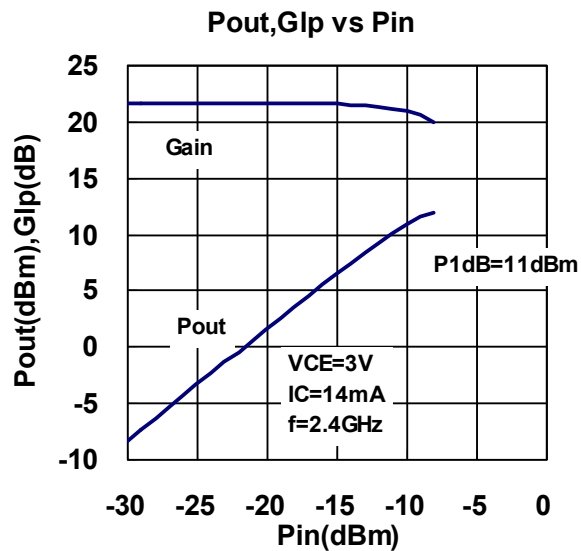
(Conditions: VCE=3V, IC=14mA, Ta=25deg.C)

f (GHz)	S11		S21		S12		S22		K	MAG/MSG (dB)
	Mag.	Angle	Mag.	Angle	Mag.	Angle	Mag.	Angle		
1	0.491	-65.0	18.143	120.5	0.021	60.2	0.778	-26.4	0.57	29.3
2	0.268	-102.9	11.227	91.6	0.032	54.0	0.636	-34.3	0.91	25.4
3	0.164	-141.1	7.949	72.8	0.043	51.2	0.579	-40.5	1.07	21.1
4	0.137	173.6	6.137	57.3	0.054	47.7	0.546	-47.9	1.14	18.3
5	0.163	136.7	5.021	43.3	0.065	43.1	0.513	-56.3	1.18	16.3
6	0.203	111.4	4.254	30.4	0.077	37.9	0.491	-64.3	1.19	14.8
7	0.263	96.8	3.705	17.4	0.089	31.5	0.455	-75.1	1.18	13.6
8	0.326	85.2	3.270	5.1	0.100	24.3	0.414	-85.9	1.18	12.6
9	0.384	76.7	2.974	-6.8	0.112	16.9	0.380	-98.4	1.14	12.0
10	0.442	69.1	2.768	-19.1	0.123	9.4	0.369	-114.3	1.06	12.0
11	0.501	61.8	2.578	-32.2	0.135	0.8	0.353	-132.6	0.98	12.8
12	0.552	54.2	2.401	-45.8	0.145	-7.9	0.354	-154.5	0.92	12.2
13	0.579	46.2	2.235	-58.3	0.154	-17.8	0.358	-174.7	0.89	11.6
14	0.611	39.3	2.134	-72.9	0.164	-28.0	0.405	166.5	0.78	11.1
15	0.627	31.7	1.953	-88.1	0.167	-38.8	0.452	146.0	0.74	10.7
16	0.620	24.2	1.762	-102.2	0.169	-47.9	0.490	127.0	0.78	10.2
17	0.633	18.8	1.579	-115.7	0.178	-56.6	0.503	109.3	0.78	9.5
18	0.645	13.1	1.395	-126.1	0.180	-66.2	0.514	96.8	0.80	8.9

Recommended foot pattern;FR4($\epsilon_r=4.6@1\text{MHz}$, $t=0.8\text{mm}$)

(Reference data)

TYPICAL CHARACTERISTICS (Ta=25°C)



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